High-Current Complementary Silicon Power Transistors

- . . . designed for use in high-power amplifier and switching circuit applications,
- High Current Capability I_C Continuous = 60 Amperes
- DC Current Gain hFE = 15-100 @ IC = 50 Adc
- Low Collector-Emitter Saturation Voltage -VCE(sat) = 2.5 Vdc (Max) @ IC = 50 Adc

MAXIMUM RATINGS

Rating	Symbol	MJ14001	MJ14002 MJ14003	Unit
Collector–Emitter Voltage	VCEO	60	80	Vdc
Collector Base Voltage	V _{CBO}	60	80	Vdc
Emitter-Base Voltage	V _{EBO}		5 60	
Collector Current — Continuous	IC	6		
Base Current — Continuous	ΙΒ	1	5	Adc
Emitter Current — Continuous	ΙΕ	7	5	
Total Power Dissipation @ T _C = 25°C Derate above 25°C	PD	300 17		Watts W/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	−65 to	+200	°C

THERMAL CHARACTERISTICS

	Characteristic	Symbol	Max	Unit
ı	Thermal Resistance, Junction to Case	$R_{\theta JC}$	0.584	°C/W

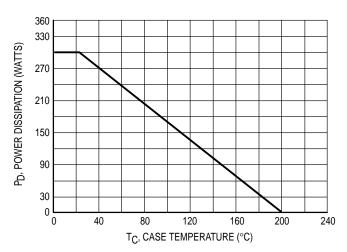


Figure 1. Power Derating

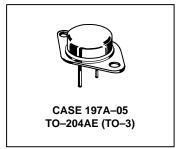
Preferred devices are Motorola recommended choices for future use and best overall value.

REV 2

NPN MJ14002* **PNP MJ14001** MJ14003*

*Motorola Preferred Device

60 AMPERES COMPLEMENTARY SILICON POWER TRANSITORS 60-80 VOLTS **300 WATTS**





MJ14002 MJ14001 MJ14003

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS				•	•
Collector–Emitter Sustaining Voltage (1) (I _C = 200 mAdc, I _B = 0)	MJ14001 MJ14002, MJ14003	VCEO(sus)	60 80	_	Vdc
Collector Cutoff Current ($V_{CE} = 30 \text{ Vdc}, I_{B} = 0$) ($V_{CE} = 40 \text{ Vdc}, I_{B} = 0$)	MJ14001 MJ14402, MJ14003	ICEO		1.0 1.0	mA
Collector Cutoff Current (VCE = 60 Vdc, VBE(off) = 1.5 V) (VCE = 80 Vdc, VBE(off) = 1.5 V)	MJ14001 MJ14002, MJ14003	ICEX		1.0 1.0	mA
Collector Cutoff Current ($V_{CB} = 60 \text{ Vdc}, I_{E} = 0$) ($V_{CB} = 80 \text{ Vdc}, I_{E} = 0$)	MJ14001 MJ14002, MJ14003	ICBO		1.0 1.0	mA
Emitter Cutoff Current (VBE = 5 Vdc, I _C = 0)		^I EBO	_	1.0	mA
ON CHARACTERISTICS				•	•
DC Current Gain (1) (I _C = 25 Adc, V _{CE} = 3.0 V) (I _C = 50 Adc, V _{CE} = 3.0 V) (I _C = 60 Adc, V _{CE} = 3.0 V)		hFE	30 15 5	_ 100 _	_
Collector–Emitter Saturation Voltage (1) (I _C = 25 Adc, I _B = 2.5 Adc) (I _C = 50 Adc, I _B = 5.0 Adc) (I _C = 60 Adc, I _B = 12 Adc)		^V CE(sat)	_ _ _ _	1 2.5 3	Vdc
Base–Emitter Saturation Voltage (1) (I _C = 25 Adc, I _B = 2.5 Adc) (I _C = 50 Adc, I _B = 5.0 Adc) (I _C = 60 Adc, I _B = 12 Adc)		VBE(sat)	_ _ _	2 3 4	Vdc
DYNAMIC CHARACTERISTICS					
Output Capacitance (V _{CB} = 10 Vdc, I _E = 0, f = 0.1 MHz)		C _{ob}	_	2000	pF

⁽¹⁾ Pulse Test: Pulse Width = 300 μ s, Duty Cycle \leq 2%.

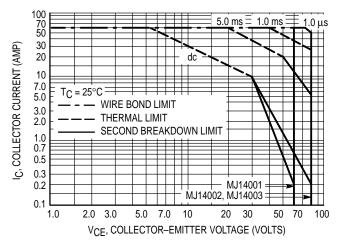


Figure 2. Maximum Rated Forward Biased Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_{\text{C}} - V_{\text{CE}}$ limits of the transistor that must be observed for reliable operation: i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 2 is based on $T_{J(pk)} = 200^{\circ}C$; T_{C} is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \le 200^{\circ}C$. $T_{J(pk)}$ may be calculated from the data in Figure 13. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

TYPICAL ELECTRICAL CHARACTERISTICS

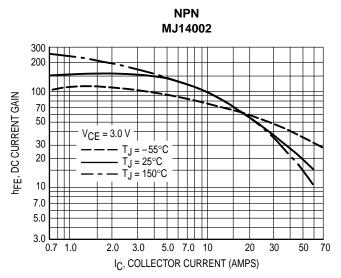


Figure 3. DC Current Gain

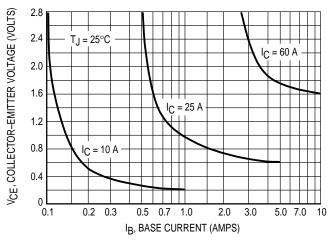


Figure 5. Collector Saturation Region

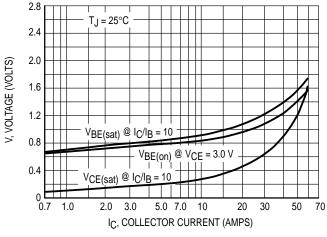


Figure 7. "On" Voltages

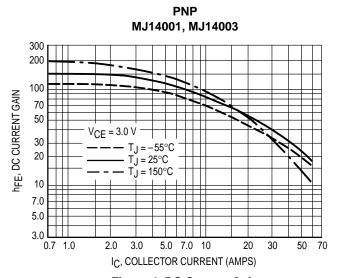


Figure 4. DC Current Gain

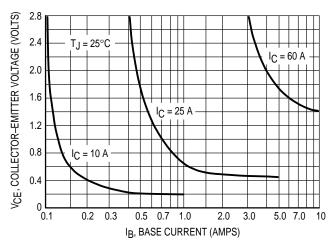


Figure 6. Collector Saturation Region

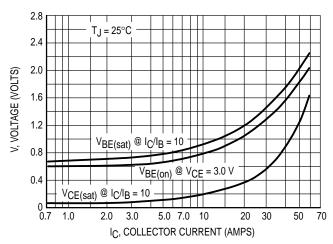


Figure 8. "On" Voltages

MJ14002 MJ14001 MJ14003

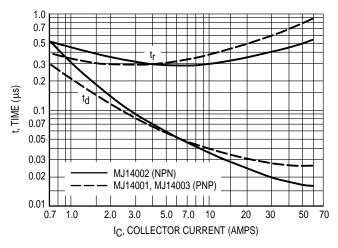


Figure 9. Turn-On Switching Times

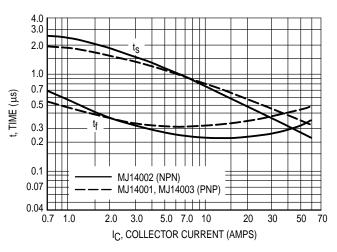


Figure 10. Turn-Off Switching Times

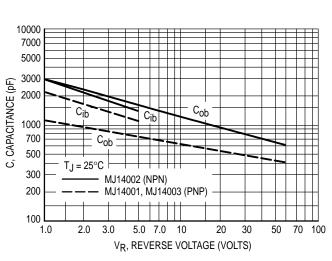
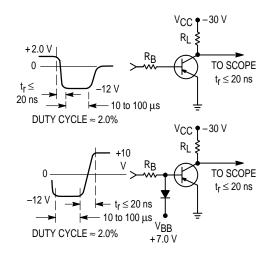


Figure 11. Capacitance Variation



FOR CURVES OF FIGURES 3 & 6, RB & RL ARE VARIED. INPUT LEVELS ARE APPROXIMATELY AS SHOWN. FOR NPN CIRCUITS, REVERSE ALL POLARITIES.

Figure 12. Switching Test Circuit

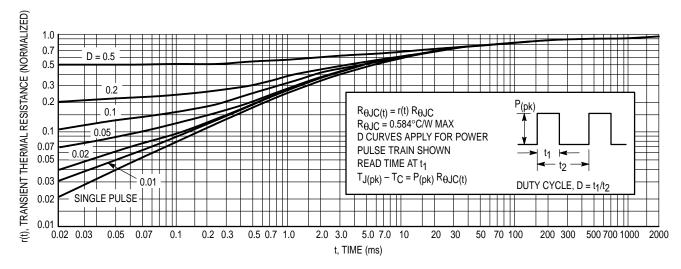
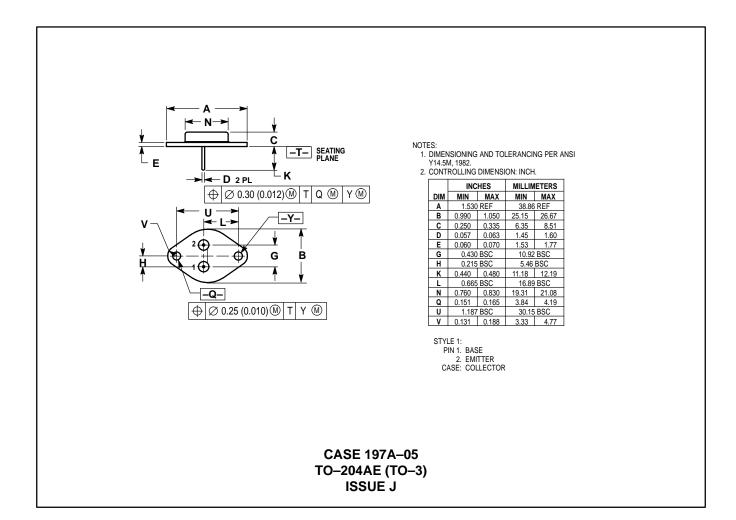


Figure 13. Thermal Response

PACKAGE DIMENSIONS



MJ14002 MJ14001 MJ14003

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